

1. Scope :

This specification applies to PIN silicon photodiode chips
Device No. PD-30235-B.

2. Structure :

2-1. Planar type : PIN Diode.

2-2. Electrodes :

Top side (Anode) : Aluminum alloy.

Top side (Cathode) : Aluminum alloy.

Backside (Cathode) : Gold.

3. Size :

3-1. Chip size(including scribe lane) :259.8 mils × 212.5 mils (6.6 mm × 5.4 mm).

3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm)

3-3. Active area of a single large PD(A1) : 53.34 mils ×33.85 mils (**1.355 mm × 0.86 mm**).

3-4. Active area of a single large PD(A2) : 55.31 mils ×35.43 mils (**1.405 mm × 0.90 mm**).

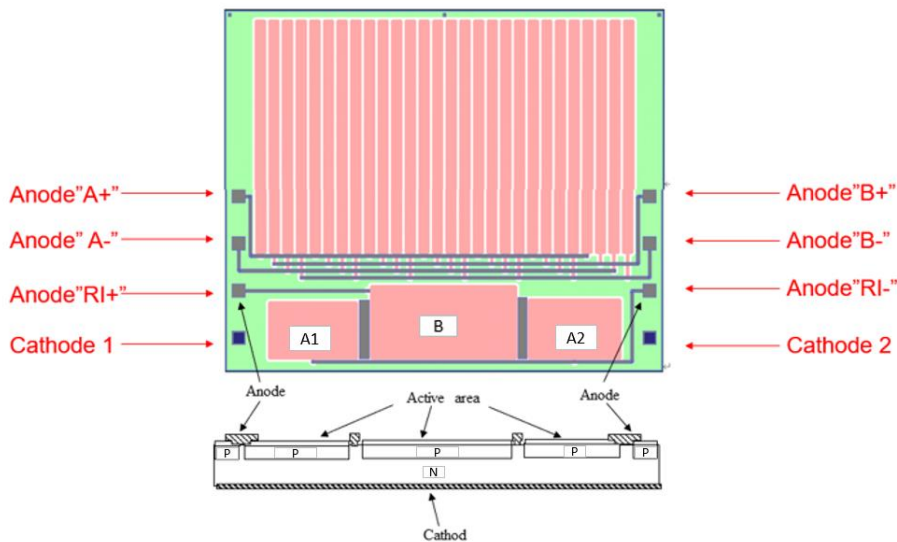
3-5. Active area of a single large PD(B) : 87.00 mils ×43.30 mils (**2.210 mm × 1.10 mm**).

3-6. Active area of a group of single small PD : 6.49 mils ×137.79 mils ×7(**0.165 mm×3.50 mm×7**)

3-7. Bonding pad (Anode) : 7.87 x7.87 mils (0.20 x 0.20 mm).

3-8. Bonding pad (Cathode) : 7.87 x7.87 mils (0.20 x 0.20 mm).

3-9. Pattern drawing : Refer to the attached drawing.



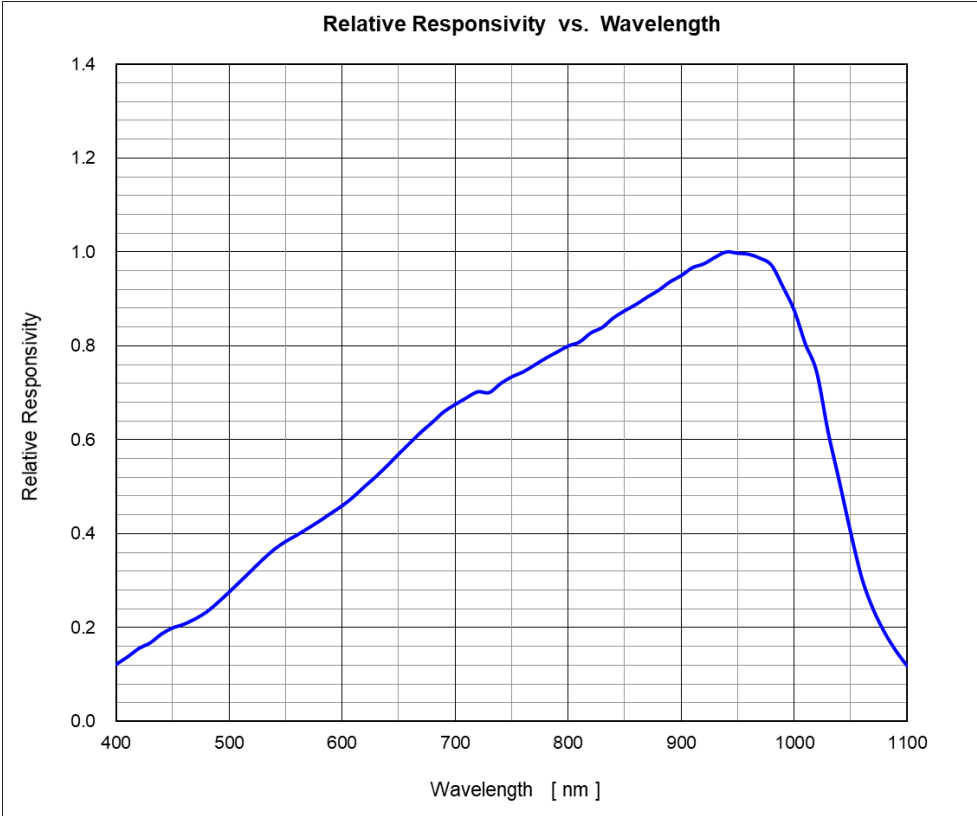
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark current	ID	VR=5V Ee=0mW/cm ²			5	nA
*Reverse breakdown voltage	V(BR)R	IR=100uA Ee=0mW/cm ²	40			V
*Forward Voltage	VF	IF=10mA Ee=0mW/cm ²			1.3	V

Peak wavelength of sensitivity	λ_p	---		940		nm
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*Based on 100% probing

5. Relative spectral responsivity



*Bare chip measured with integrating sphere, for reference only.